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著者	Zhao X.Y., Shi X., Chen L.D., Zhang W. Q., Bai S.Q., Pei Y.Z., Li X.Y., Goto T.
journal or	Applied Physics Letters
publication title	
volume	89
number	9
page range	092121
year	2006
URL	http://hdl.handle.net/10097/51717

doi: 10.1063/1.2345249

Synthesis of $Yb_yCo_4Sb_{12}/Yb_2O_3$ composites and their thermoelectric properties

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(Received 29 April 2006; accepted 24 July 2006; published online 1 September 2006)

Composites containing Yb-filled CoSb₃ and well-distributed Yb₂O₃ particles are synthesized by *in situ* reaction method. The structural, chemical, and transport properties of the composites are studied. Some Yb₂O₃ particles with microsize locate at the grain boundaries of matrix and others distribute within Yb_yCo₄Sb₁₂ grains as nanoscale inclusions. The combination of the "rattling" of Yb ions inside the voids of CoSb₃ and the phonon scattering of the oxide defects results in a remarkable reduction in the lattice thermal conductivity. The thermoelectric performance of the composites is significantly improved, and the maximum figures of merit reach 1.3 for the Yb_{0.25}Co₄Sb₁₂/Yb₂O₃ and 1.2 for the Yb_{0.21}Co₄Sb₁₂/Yb₂O₃ composites at 850 K. © 2006 American Institute of Physics. [DOI: 10.1063/1.2345249]

During the last decade, intensive effort has been made in searching for high performance thermoelectric materials. The performance of thermoelectric materials is characterized by the figure of merit $ZT = \alpha^2 \sigma T / \kappa$ where α , σ , $\kappa (\kappa = \kappa_E + \kappa_L)$, and T are the Seebeck coefficient, the electrical conductivity, the total thermal conductivity of the material, and the absolute temperature, respectively. CoSb3-based filled skutterudites have been attracting considerable attention for their potential thermoelectric applications.^{1–3} A series of p- and *n*-type filled skutterudites with high ZT's have been reported.¹⁻⁵ Unfortunately, the lattice thermal conductivities (κ_L) of the filled skutterudites, especially for *n*-type partially filled CoSb₃ skutterudites, still remain relatively high as compared with the state-of-the-art thermoelectric materials, such as Bi₂Te₃-based alloys. Further reduction of κ_I for the filled skutterudites is an effective approach to improve the thermoelectric performance of the filled CoSb₃.

Experimentally, it was shown that the κ_L of CoSb₃-based materials could be depressed dramatically by introducing fullerene (C_{60}) large defects into matrix, and a significant enhancement of ZT was observed in a wide temperature range.⁶ A marked reduction in κ_L was also obtained by adding a small amount of ZrO₂ nanoparticles into ZrNiSn-based matrix.⁷ These extra defects are believed to be inertial to electrical transport and therefore have little influence on the electrical transport properties of the matrix.^{6,7} Thus, it is reasonable to assume that oxides, especially rare-earth (RE) oxides which form simultaneously during the synthesis of filled CoSb₃ skutterudites, may be good candidates for the reduction of κ_L . Furthermore, both theoretical⁸ and experimental^{2,9–12} studies already showed that Yb had a relatively high filling fraction in CoSb₃. Experimental work also demonstrated that Yb-filled skutterudites with filling fraction of about 0.2 possessed ZT close to 1 at 600-750 K.^{2,9,10} Therefore, it is expected that composites containing the filled CoSb₃ with higher Yb filling fractions and distributed Yb₂O₃ defects should have higher thermoelectric performance. In this letter, we report the synthesis and the thermoelectric properties of the $Yb_yCo_4Sb_{12}/Yb_2O_3$ composites by an *in situ* reaction method.

Details on the preparation of filled skutterudite samples were described in our earlier paper.⁵ To achieve the Yb oxide, an excessive Yb metal was used and a proper annealing time was adopted during the preparation process. The final solid products were ground into fine powders in the air above 30 min for oxidizing the remainder Yb metal. The obtained powders were then sintered by spark plasma sintering at 850 K for 15 min in a graphite die to form dense pellets. Structural and chemical compositions of the polycrystalline samples were characterized by x-ray diffraction (XRD) and electron microprobe analyses (EPMA). The compositions of the Yb-filled skutterudite phases were then obtained from EPMA normalized to the full occupancy of the cobalt sites. Experimental procedures for electrical and thermal transport measurements were described elsewhere.⁵

Several Yb-filled CoSb₃ samples are prepared, and only two of them with relatively high filling fractions of Yb contain Yb₂O₃ particles in the matrix. Our XRD and EPMA show that the Yb_{0.21}Co₄Sb₁₂/Yb₂O₃ and Yb_{0.25}Co₄Sb₁₂/Yb₂O₃ composites are obtained with a trace amount of impurity phases of Sb, CoSb₂, and YbSb₂. Table I lists the chemical composition and some physical properties for all the samples at room temperature. The carrier concentrations for YbvCo4Sb12 with low Yb filling fractions (y =0.10, 0.15) in this work and those for the reported $Yb_{\nu}Co_4Sb_{12}$ compounds² are nearly in a linear relation to the filling fraction of Yb in CoSb₃. The carrier concentrations of the two composite samples are relatively high, due to the high filling fraction and probably the existence of impurity phases (YbSb₂ and CoSb₂) in the samples. Our data also indicate that the maximum filling fraction of Yb in CoSb₃ is about 0.25 without any charge compensation, which is consistent with both the previous experimental^{2,9-11} and the theoretical⁸ results.

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TABLE I. Summary of composition and some physical properties of Ybfilled skutterudites with and without oxide particles at room temperature. n, a, κ_L and ρ^* are the carrier concentration, lattice constant, the lattice thermal conductivity, and the relative density of the samples, respectively.

Systems	$n (10^{20}/\text{cm}^{-3})$	a (Å)		$ ho^* (\%)$
Yb _{0.10} Co ₄ Sb _{12.77}	1.0	9.043	3.49	98.5
Yb _{0.15} Co ₄ Sb _{12.81}	1.6	9.047	2.75	97.9
Yb _{0.21} Co ₄ Sb _{12.65} /Yb ₂ O ₃	3.3	9.053	2.04	97.4
Yb _{0.25} Co ₄ Sb _{12.69} /Yb ₂ O ₃	8.4	9.056	1.72	97
Yb _{0.19} Co ₄ Sb ₁₂ ^a	1.9	9.051	2.6	
Yb _{0.46} Co ₄ Ge _{0.79} Sb _{11.21} ^a	2.0		2.2	

^aReference 12.

Figure 1 shows the backscattered electron image (a), the x-ray maps of oxygen (b) and Yb (c), and the transmission electron microscopy (TEM) image (d) of a nano-oxide particle in the composites. The gray area in Fig. 1(a) is the Yb_{0.25}Co₄Sb₁₂ phase, and the white places are the defects. The x-ray maps of oxygen and Yb [Fig. 1(b) and 1(c)] identify that the defects are mainly Yb₂O₃. A small amount of YbSb₂ is also observed together with the appearance of Yb₂O₃. Yb₂O₃ agglomerates into irregular clusters of different sizes located at the grain boundaries of the matrix. The average size of Yb₂O₃ defects is normally large due to the high nominal Yb concentration in the preparation of samples. There is also a large number of small white areas in multiplicated EPMA pictures, indicating the existence of Yb_2O_3 defects with less than microsize in the matrix. The presence of many Yb₂O₃ inclusions is also detected inside individual matrix grains with the size of about 20 nm or more as shown in Fig. 1(d). The content of Yb₂O₃ in Yb_{0.25}Co₄Sb₁₂/Yb₂O₃ composite is higher than that in Yb_{0.21}Co₄Sb₁₂/Yb₂O₃ composite.

The temperature dependences of electrical conductivity (σ) , Seebeck coefficient (α) , and power factor $(\alpha^2 \sigma)$ for all samples between 300 and 850 K are shown in Fig. 2. σ shows a metallic behavior over the entire temperature range for all samples. The absolute value of α deceases with increasing Yb filling fraction, due to the increase of carrier



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FIG. 2. Temperature dependences of the electrical conductivity (a), Seebeck coefficient (b), and power factor (c) for $Yb_yCo_4Sb_{12}$ compounds and $Yb_yCo_4Sb_{12}/Yb_2O_3$ composites.

concentration (Table I). α also increases with increasing temperature except for the Yb_{0.10}Co₄Sb₁₂ compound. Notice that all the samples exhibit relatively large α , similar to the reported data for CoSb₃-based *n*-type filled skutterudites.^{2–5,9–12} High $\alpha^2 \sigma$ for the composites are achieved [Fig. 2(c)], especially with a value of 47 μ W/cm K² for Yb_{0.25}Co₄Sb₁₂/Yb₂O₃ at 850 K, identifying that these composites keep good electrical transport properties.

Figure 3 plots κ_L as a function of the Yb filling fraction at room temperature for all samples. κ_L values are estimated by subtracting the electronic contribution κ_E from the total thermal conductivity. The Weidemann-Franz relation with Lorentz constant of $L_0 = 2.0 \times 10^{-2} \text{ V/K}^2$ is applied to estimate $\kappa_E(=L_0\sigma T)$. κ_L for single phased Yb-filled skutterudite compounds are close to the reported values with similar Yb filling fractions.^{2,12} For both $Yb_{0.21}Co_4Sb_{12}/Yb_2O_3$ and $Yb_{0.25}Co_4Sb_{12}/Yb_2O_3$ composites, however, κ_L are much lower than those of the Yb_vCo₄Sb₁₂ compounds with the Yb filling fractions. The similar κ_L of the Yb_{0.25}Co₄Sb₁₂/Yb₂O₃ composite is about 1.72 W/m K at room temperature and decreases to 0.52 W/m K at 800 K (inset in Fig. 3), approaching the limit of the theoretical



FIG. 1. (Color online) Backscattered electron image (a) and x-ray maps for oxygen (b) and Yb (c) in the Yb_{0.25}Co₄Sb₁₂/Yb₂O₃ composite. (d) shows the TEM image of a typical Yb₂O₃ nano-oxide particle in the Yb_{0.21}Co₄Sb₁₂/Yb₂O₃ composite.

FIG. 3. Lattice thermal conductivity (κ_L) at room temperature as a function of the Yb filling fraction for Yb_yCo₄Sb₁₂ compounds and Yb_yCo₄Sb₁₂/Yb₂O₃ composites. Insert: Temperature dependence of κ_L for

Yb_{0.21}Co₄Sb₁₂/Yb₂O₃ composite. Downloaded 01 Sep 2011 to 130.34.134.250. Redistribution subject to AIP license or copyright; see http://apl.aip.org/about/rights_and_permissions



FIG. 4. Temperature dependence of ZT for $Yb_yCo_4Sb_{12}$ compounds and $Yb_yCo_4Sb_{12}/Yb_2O_3$ composites. ZT from others are also indicated in the figure.

value, 0.3 W/m K.^{13} The minimum of the κ_L Yb_{0.21}Co₄Sb₁₂/Yb₂O₃ composite at room temperature is about 22% lower than that of Yb_{0.19}Co₄Sb₁₂ reported by Nolas and co-workers,^{2,12} although the Yb filling fractions for them are close to each other. The decrease of κ_L in the composites should be attributed to the oxide defects, which provide additional phonon scattering. Unlike the $CoSb_3/C_{60}$ composites where lattice phonons are mainly scattered by the large defects of fullerene,⁶ both the large oxide defects located at grain boundaries and the nanoscale inclusions distributed in matrix grains give rise to phonon scattering and lower κ_L for the Yb_vCo₄Sb₁₂/Yb₂O₃ composites.^{7,14} For now, we could not quantitatively estimate the different contributions from either the large oxide defects or the nanoscale inclusions to the reduction of κ_L . But, because the size of the large oxide defects is well beyond the mean free path of phonons in CoSb₃,⁶ we believe that the significant reduction of κ_L could be mainly attributed to the phonon scattering by the nanoscale Yb₂O₃ inclusions in matrix grains.

Figure 4 displays the calculated dimensionless figures of merit (*ZT*) versus the temperature for all samples. The data from Nolas *et al.*, Sales *et al.*, and Anno *et al.* are also included in Fig. 4 for comparison. It is obvious that the *ZT* values of the composites are enhanced in comparison with the reported values of $Yb_yCo_4Sb_{12}$ compounds. *ZT*=1.3 is achieved for $Yb_{0.25}Co_4Sb_{12}/Yb_2O_3$ composite at 850 K and ranks as one of the highest *ZT* values reported so far for *n*-type skutterudites. This encouraging result illustrates firmly the potential of filled skutterudite composites as an advanced thermoelectric material in the intermediate temperature range.

In summary, Yb_2O_3 particles with different sizes were introduced into the Yb-filled skutterudites to form composite materials by *in situ* reaction method, and the effect of the oxide particles on the thermoelectric properties of the composites was investigated. The Yb₂O₃ particles depress the κ_L of the composites to come close to the minimum thermal conductivity of filled CoSb₃ and are essential to achieve a high ZT for the composites. Our study implies that introducing RE oxide additions into the matrix through methods such as *in situ* reaction is helpful in essentially improving ZT for conventional filled skutterudites, even though they already have good thermoelectric performance. We also like to address that the extra RE oxide particles are formed simultaneously during the synthesis of the filled CoSb₃ and that the RE_vCo₄Sb₁₂/RE oxide composites are thermodynamically stable at elevated temperature in comparison with many other nanocomposite materials containing only the nanoparticles of CoSb₃ itself, and therefore they should have many practical applications.

The authors acknowledge financial supports from NSFC under Grant Nos. 50325208 and 50310353, and the Ministry of Science and Technology of china through 973-project under Grant No. 2007CB607502. One of the authors (L.D.C.) acknowledges the support from IFCAM-IMR of Tohoku University, Japan.

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